1 GENERAL INFORMATION

1.1 INTRODUCTION

In this section, we shall give some background information of the 4 point probe techniques, the applications, CDE ResMap's role in this field and other semi-technical information.

1.1.1 What is a 4 point probe?

A 4 point probe [4pp] resistivity measurement tool is a precision instrument for measuring resistivity in a conductive media (usually a thin film the semiconductor applications), called sheet resistivity, Rs. The unit expressed is generally called Ω/\Box or ohms per square. The symbol \Box , or square, is not a unit like cm², it is just a way to express the measure of a sheet or semilarge area (compared with the dimension of a probe).

The 4 point probe has 4 pins [#1, 2, 3 & 4] in contact with the conductor sample. Two pins apply a current and the voltage is measured across the other two pins. For our applications, the 4 pins are in a straight line with equal spacing (typical 1-mm). The pins are made of metal, typically Tungsten Carbide, with a pointed tip. The tips have typical radii of between $40 \mu m$ (0.0016" or 1.6 mils) to $500 \mu m$ (20 mils). The pins are located in a housing called a probe. It is loaded axially with springs, with forces of typically 100 gms. When the pins are pressed onto the sample, the spring is compressed so the pins are retracted (pushed) into the housing in order to make a good electrical contact for measurement. Later, we will show that this contact is very important.

If one puts a current I_{14} between pins 1 and 4, the measured voltage between pins 2 and 3 is V_{23} , then the sheet resistivity is,

$$Rs = \pi/ln2 \cdot V_{23}/I_{14} = 4.532 V_{23}/I_{14}$$

Modern techniques allow measurement of Rs to a very high accuracy ($\leq \pm 0.5\%$) and very high precision (Repeatability $\leq \pm 0.1\%$).

1.1.2 Types of measurements

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The 4 point probe measures sheet resistivity Rs directly for many applications such as implant film, metal film, etc. one either adopt or forces to adopt Rs as the native unit.

However, one can derive other units such as film thickness w, media bulk resistivity ρ or other types of measurements.

1.1.2.1 Film thickness

Since the thickness of a metal film cannot be measured optically like a dielectric film because it is, in general, not transparent to light, so the resistivity measurement can be used to calculate film thickness. If one assumes the film behaves like a bulk (or the electrical and mechanical properties do not change in the film), then one can express the thickness, $w = \rho \ Rs^{-1}$, where ρ is the bulk resistivity. However, many films do not behave nicely and ρ is not a constant within the thickness of the film. If we assume that ρ decreases as a function of thickness buildup (typical within the first few hundred Angstroms) then one can express $w = \rho' \ Rs^{\beta}$. As an example for CVD W film, the thickness can be expressed as $w = 1950.1 \ Rs^{-0.65567}$, over certain ranges of thickness [w in Å, and Rs in Ω/\square]. Following is a table of commonly used parameters as provided by Sematech, after much characterization:

<u>Film</u>	ρ'	Β	
Ti	3652.99	- 0.689	
TiN	3233.58	- 0.629	
W	1950.1	- 0.65567	
Al	337.17	- 0.92041	
Cu	479.13	- 0.75681	
	$w = \rho' Rs^{\beta}$		

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Although people are used to expressing Rs as basic measurement unit for metal films, for film removal such as etch back or CMP process, if one wants to find out removal rate and uniformity, one cannot subtract Rs directly. One need to first convert the measurement to film thickness before subtracting.

1.1.2.2 Bulk resistivity.

Other applications of the four point porbe are for measuring the bulk resistivity, ρ , since $\rho = \text{Rs x w}$.

For manufacturers of doped bare Silicon wafers, w, the thickness of the wafer, can be measured mechanically, then one can calculate ρ when Rs is measured.

For EPI films, one can also measure ρ . In this case the EPI thickness w is measured typically with an FTIR type instrument.

1.2 ResMap Models

The CDE ResMaps are a series of automatic resistivity mapping systems for various applications. The models and specifications are listed in the following table:

CDE ResMap 4 Point Probe Product Comparisons

Model	ResMap 168	ResMap 178	ResMap 273	ResMap 268- SMIF	ResMap 188
Feature:	Auto Cassette Load	Manual Load "Baby"	Manual Load 12" ('Big')	Integrated 8" SMIF	Flat Panel
Wafer Size:	4" - 8" C-C 2"- 8" Manual	2" - 8"	2" - 12"	8" Auto SMIF, 2"-8" manual	22" x 26" 550mm x 650mm
Max Dia. Round Sample: Max Square Sample:	8.2" 5.8" x 5.8"	8.2" 5.8" x 5.8"	12.1" 8.5" x 8.5"	8.5" 6" x 6"	
Typical Measurement Time:	1-sec per site	1-sec per site	1.5-sec per site	1-sec per site	2-sec per site
Typical Wafer Transport time (each way):	10-sec	N.A.	N.A.	10-sec	N.A.
Throughput	40 wafers/hour 49-sites	1-min per wafer 49-sites	1.5-min per wafer 49-sites	40 wafers/hour 49-sites	
Measurement Range:	$5m\Omega/\underline{} = 5M\Omega/\underline{}$	5mΩ/= - 5MΩ/=	5mΩ/= – 5MΩ/_	5mΩ/= – 5MΩ/=	5mΩ/_ – 5MΩ/¯
Repeatability [10] Same Spot: Multiple Sites Nearby:	< ±0.02% < ±0.1%				
Accuracy:	< ±0.5%	< ±0.5%	< ±0.5%	< ±0.5%	< ±0.5%
Minimum Edge Exclusion:	< 3-mm	< 3-mm	< 3-mm	< 3-mm	< 7-mm
Size: Width x Height x Depth	12"W x 10"H x 28"D	12"W x 11"H x 19"D	15"W x 110"H x 19"D	17"W x 68"H x 30"D	26"W x 8"H x 343"D
AC power:	100V to 240V				
Computer System:	Pentium 75MHz 3.5FD >500HD Color VGA Color Injet Printer	Pentium 75MHz 3.5FD >500HD Color VGA Color Injet Printer	Pentium 75MHz 3.5FD >500HD Color VGA Color Injet Printer	Pentium 75MHz 3.5FD >500HD Color VGA Color Injet Printer	Pentium 75MHz 3.5FD >500HD Color VGA Color Injet Printer
Mapping Patterns:	Polar, Rectangular, Line, User defined	Polar, Rectangular, Line, User defined	Polar, Rectangular, Line, User defined	Polar, Rectangular, Line, User defined	Rectangular, Line, User defined
Plots:	Contour, 3D, Linear, Data on points, Histogram				